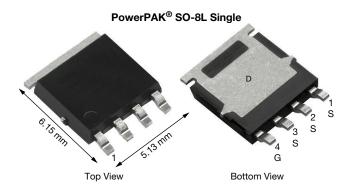


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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-40
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0140
$R_{DS(on)}(\Omega)$ at $V_{GS} = -4.5 \text{ V}$	0.0200
I <sub>D</sub> (A)	-30
Configuration	Single
Package	PowerPAK SO-8L

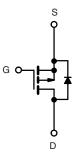
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-source voltage		$V_{DS}$	-40	V	
Gate-source voltage		V <sub>GS</sub>	± 20		
Continuous drain current	T <sub>C</sub> = 25 °C <sup>a</sup>	1	-30		
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-23		
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	-30	Α	
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-120		
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-25		
Single pulse avalanche energy	L=0.11IIII	E <sub>AS</sub>	31.2	mJ	
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	В	45	14/	
	T <sub>C</sub> = 125 °C	$P_{D}$	15	W	
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	۰.	
Soldering recommendations (peak temperature) d, e			260	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount c	$R_{thJA}$	70	°C/W
Junction-to-case (drain)		$R_{thJC}$	3.3	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). For PowerPAK SO-8L, the end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



# Vishay Siliconix

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						I.	
Drain-source breakdown voltage	V <sub>DS</sub>	V <sub>GS</sub>	= 0, I <sub>D</sub> = -250 μA	-40	-	-	.,
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1	
Zero gate voltage drain current	I <sub>DSS</sub>		V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-150	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \ge -5 \text{ V}$	-30	-	-	Α
	, ,	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A	-	0.0115	0.0140	
During and the second and		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 125 °C	-	-	0.0219	
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -10 A, T <sub>J</sub> = 175 °C	-	-	0.0261	Ω
			I <sub>D</sub> = -6 A	-	0.0163	0.0200	1
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> =	-15 V, I <sub>D</sub> = -10 A	-	37	-	S
Dynamic <sup>b</sup>						I.	
Input capacitance	C <sub>iss</sub>			-	4405	6000	
Output capacitance	C <sub>oss</sub>	V <sub>GS</sub> = 0 V	$V_{DS} = -25 \text{ V, f} = 1 \text{ MHz}$	-	248	350	рF
Reverse transfer capacitance	C <sub>rss</sub>			-	234	320	
Total gate charge c	$Q_{g}$			-	63	95	
Gate-source charge c	Q <sub>gs</sub>	V <sub>GS</sub> = -10 V	$V_{DS} = -20 \text{ V}, I_{D} = -2.5 \text{ A}$	-	9.5	-	nC
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	9.5	-	
Gate resistance	R <sub>g</sub>		f = 1 MHz	2	4.6	7	Ω
Turn-on delay time c	t <sub>d(on)</sub>			-	12	20	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub>	= -20 V, $R_1 = 8 \Omega$	-	4	10	
Turn-off delay time c	t <sub>d(off)</sub>		$V_{GEN} = -10 \text{ V}, R_g = 1 \Omega$	-	67	110	ns
Fall time <sup>c</sup>	t <sub>f</sub>			-	17	30	
Source-Drain Diode Ratings and Char	acteristics b						
Pulsed current <sup>a</sup>	I <sub>SM</sub>				-	-120	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> =	-10 A, V <sub>GS</sub> = 0 V	-	-0.82	-1.2	V
Body diode reverse recovery time	t <sub>rr</sub>			-	26	55	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	7	- A -1:/-1+ 100 A/	-	21	50	nC
Reverse recovery fall time	ta	$I_F = -2.5$	5 A, di/dt = 100 A/µs	-	15	-	
Reverse recovery rise time	t <sub>b</sub>	7		-	11	-	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-1.6	-	Α

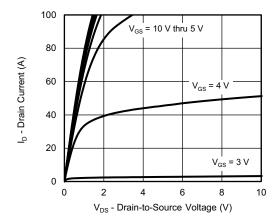
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

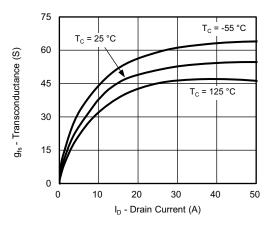
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



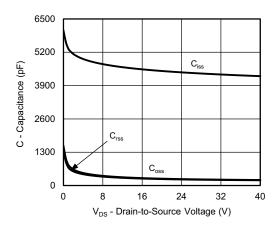
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



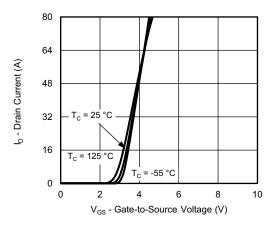
### **Output Characteristics**



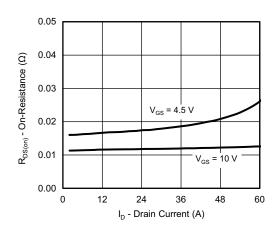
Transconductance



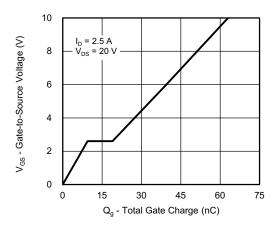
Capacitance



**Transfer Characteristics** 



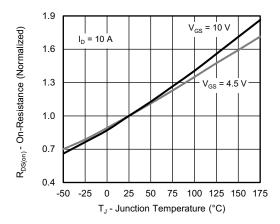
On-Resistance vs. Drain Current



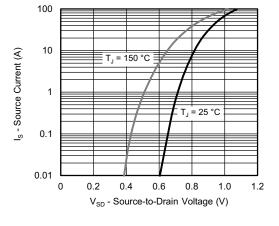
**Gate Charge** 



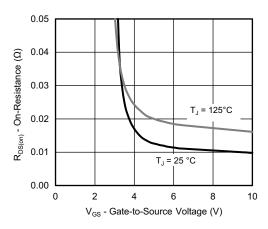
### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



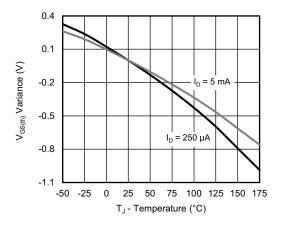
On-Resistance vs. Junction Temperature



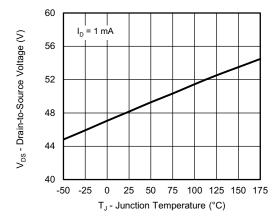
**Source Drain Diode Forward Voltage** 



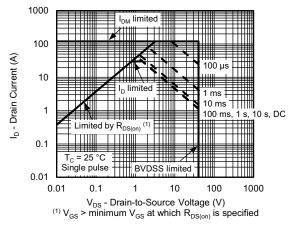
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



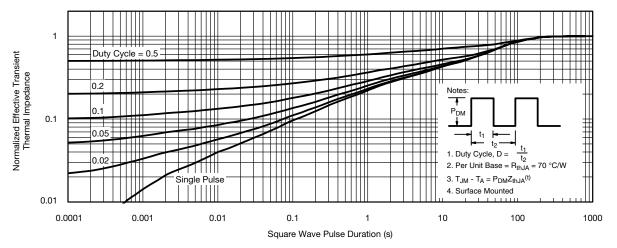
**Drain-Source Breakdown vs. Junction Temperature** 



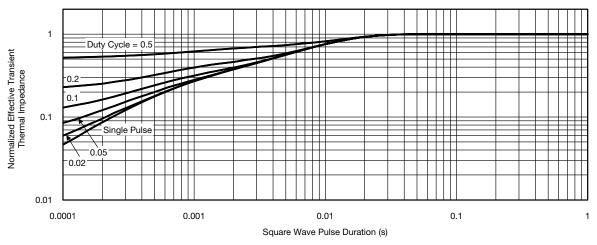
Safe Operating Area



### **THERMAL RATINGS** (T<sub>C</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

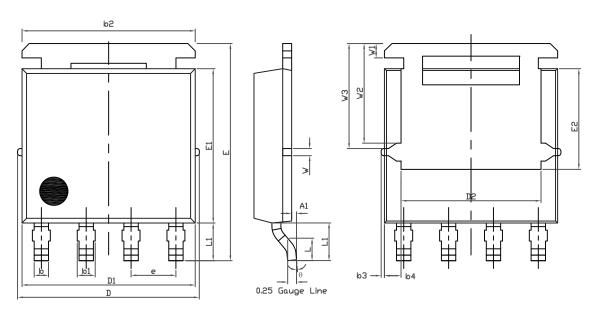
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

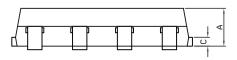
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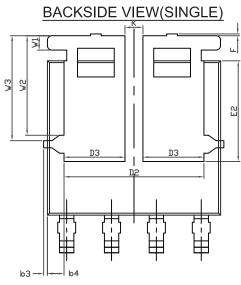


# PowerPAK® SO-8L Case Outline 2



**TOPSIDE VIEW** 





BACKSIDE VIEW(DUAL)



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DIM	MILLIMETERS			INCHES			
DIM.	MIN.	NOM.	MAX.	MIN. NOM.		MAX.	
Α	1.00	1.07	1.14	0.039	0.042	0.045	
A1	0.00	-	0.127	0.00	-	0.005	
b	0.33	0.41	0.48	0.013	0.016	0.019	
b1	0.44	0.51	0.58	0.017	0.020	0.023	
b2	4.80	4.90	5.00	0.189	0.193	0.197	
b3		0.094			0.004		
b4		0.47			0.019		
С	0.20	0.25	0.30	0.008	0.010	0.012	
D	5.00	5.13	5.25	0.197	0.202	0.207	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D3	1.63	1.73	1.83	0.064	0.068	0.072	
е		1.27 BSC		0.050 BSC			
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	2.75	2.85	2.95	0.108	0.112	0.116	
F	-	-	0.15	-	-	0.006	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
K		0.51			0.020		
W	0.23			0.009			
W1	0.41			0.016			
W2	2.82			0.111			
W3	2.96			0.117			
q	0°	-	10°	0°	-	10°	

ECN: S19-0643-Rev. B, 05-Aug-2019

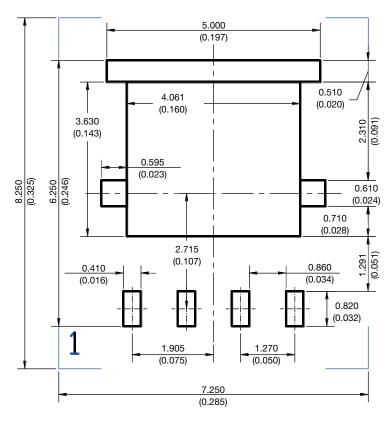
DWG: 6044

### Note

• Millimeters will gover



### RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L SINGLE



Recommended Minimum Pads Dimensions in mm (inches)



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